

TLP785, TLP785F

Office Equipment
Home Electric Appliances
Solid-State Relays
Switching Power Supplies
Contactless Controller Outputs
Simplex/Multiplex Data Transmission

The TOSHIBA TLP785 consists of a silicone phototransistor optically coupled to an infrared emitting diode in a four lead plastic DIP (DIP4) with having high isolation voltage (AC: 5000 Vrms (min)).
TLP785F is a lead forming type for the long creepage surface mounting of TLP785.

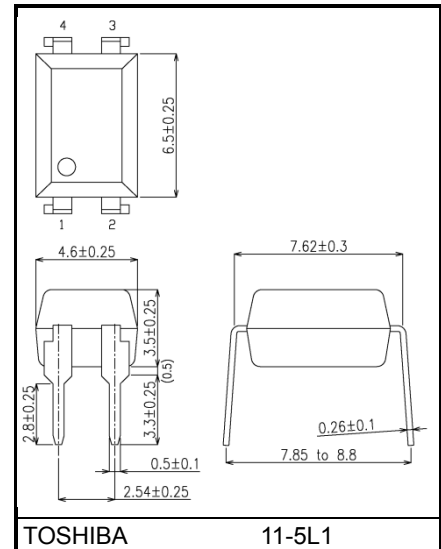
- TLP785: 7.62 mm pitch type DIP4
- TLP785F: 10.16 mm pitch type DIP4
- Collector-emitter voltage: 80 V (min)
- Current transfer ratio: 50% (min)
Rank GB: 100% (min)
- Isolation voltage: 5000 Vrms (min)
- UL-recognized : UL 1577, File No.E67349
- cUL-recognized :CSA Component Acceptance Service No.5A
File No.E67349
- VDE-approved : EN 60747-5-5 (Note 1)
- CQC-approved: GB4943.1, GB8898 China Factory
- SEMKO-approved : EN 62368-1

Note 1 : When a VDE approved type is needed,
please designate the **Option(D4)**.

- Construction mechanical rating

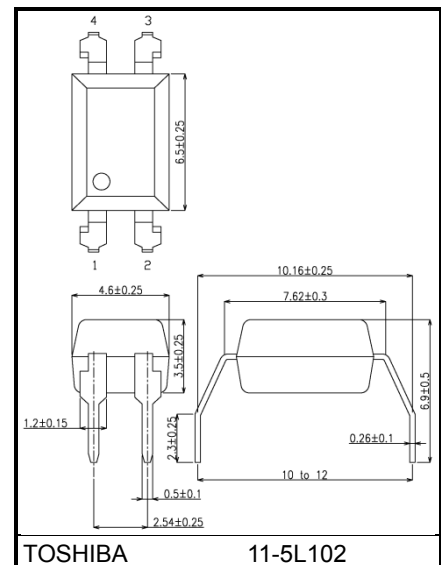
	7.62 mm Pitch Standard Type	10.16 mm Pitch TLPxxxF Type
Creepage distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation thickness	0.4 mm (min)	0.4 mm (min)
Inner creepage distance	4.0 mm (min)	4.0 mm (min)

TLP785 Unit: mm



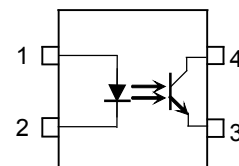
Weight: 0.25 g (typ.)

TLP785F Unit: mm



Weight: 0.25 g (typ.)

Pin Configurations (top view)



- 1 : Anode
- 2 : Cathode
- 3 : Emitter
- 4 : Collector

Start of commercial production
2010-11